Switching (60V, 200mA)

SM6K2

Features

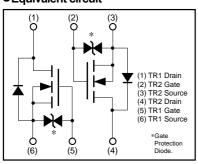
- 1) Two RHU002N06 chips in a SMT package.
- 2) Mounting possible with SMT3 automatic mounting
- 3) Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.

Structure

Silicon N-channel MOSFET transistor

The following characteristics apply to both Tr1 and Tr2.

Equivalent circuit

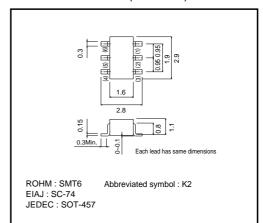


A protection diode has been built in between the gate and the source to protect against static electricity when the product is in use.

● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		Voss	60	V
Gate-source voltage		Vgss	±20	V
Б : .	Continuous	ΙD	200	mA
Drain current	Pulsed lpp*1 800	800	mA	
Drain reverse current	Continuous	Idr	200	mA
	Pulsed	IDRP*1	800	mA
Total power dissipatio	n	Pp*2 200		mW
Channel temperature		Tch	150	°C
Storage temperature		Tstg	−55~+150 °C	

●External dimensions (Units : mm)



^{*1} Pw≤10μs, Duty cycle≤1% *2 When using 1×0.75×0.062 inch glass epoxy board.

● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions	
Gate leakage current	Igss	-	_	±10	μΑ	Vgs=±20V, Vps=0V	
Drain-source breakdown voltage	V (BR) DSS	60	_	_	V	I _D =10μA, V _G s=0V	
Drain cutoff current	Ipss	_	_	1	μΑ	V _{DS} =60V, V _{GS} =0V	
Gate threshold voltage	VGS (th)	1	_	2.5	V	V _{DS} =10V, I _D =1mA	
Drain-source on-state resistance	RDS (on)*1	_	1.7	2.4	Ω	In=200mA, Vgs=10V	
		_	2.8	4.0		In=200mA, Vgs=4V	
Forward transfer admittance	I Yfs I*1	100	_	-	mS	Vps=10V, Ip=200mA	
Input capacitance	Ciss	_	15	_	pF	V _{DS} =25V V _{GS} =0V f=1MHz	
Output capacitance	Coss	_	8	_	pF		
Reverse transfer capacitance	Crss	_	4	-	pF		
Turn-on delay time	td (on)*2	_	6	_	ns	I _D =100mA, V _{DD} =30V V _{GS} =10V R _L =300Ω R _{GS} =10Ω	
Rise time	tr*2	_	5	-	ns		
Turn-off delay time	td (off)*2	_	12	-	ns		
Fall time	t _f *2	_	95	_	ns		
Total gate charge	Qg*2	_	2.2	4.4	nC	V _{DD} ≒30V V _{GS} =10V I _D =200mA	
Gate-source charge	Q _{gs} *2	_	0.6	_	nC		
Gate-drain charge	Q _{gd} *2	-	0.3	-	nC		

^{*1} Pw≤300μs, Duty cycle≤1% *2 Pulsed

Packaging specifications

	Package	Taping
	Code	T110
Туре	Basic ordering unit (pieces)	3000
SM6K2		0

• Electrical characteristic curves

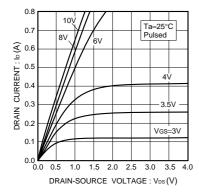


Fig.1 Typical output characteristics

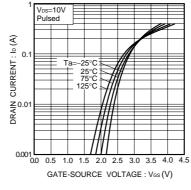


Fig.2 Typical transfer characteristics

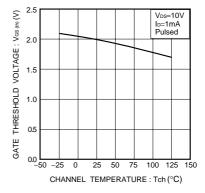
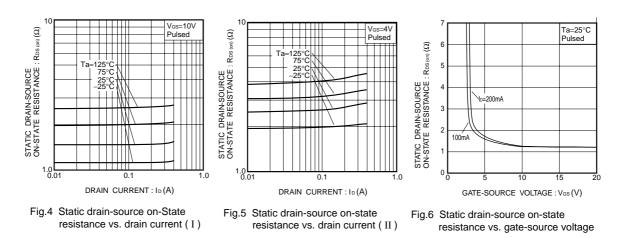


Fig.3 Gate threshold voltage vs. channel temperature





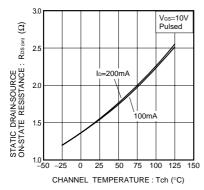


Fig.7 Static drain-source on-state resistance vs. channel temperature

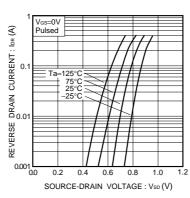


Fig.8 Reverse drain current vs. source-drain voltage (I)

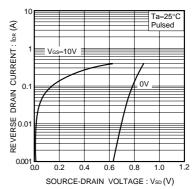


Fig.9 Reverse drain current vs. source-drain voltage (II)

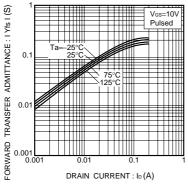


Fig.10 Forward transfer admittance vs. drain current

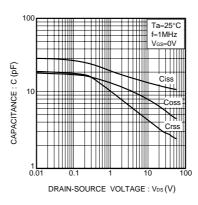


Fig.11 Typical capacitance vs. drain-source voltage

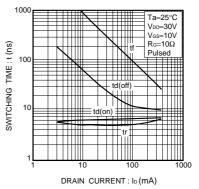


Fig.12 Switching characteristics

•Switching characteristics measurement circuit

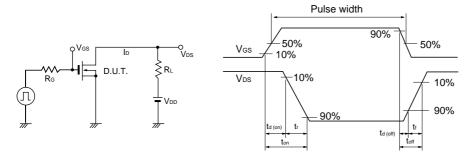


Fig.13 Switching time test circuit

Fig.14 Switching time waveforms

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